

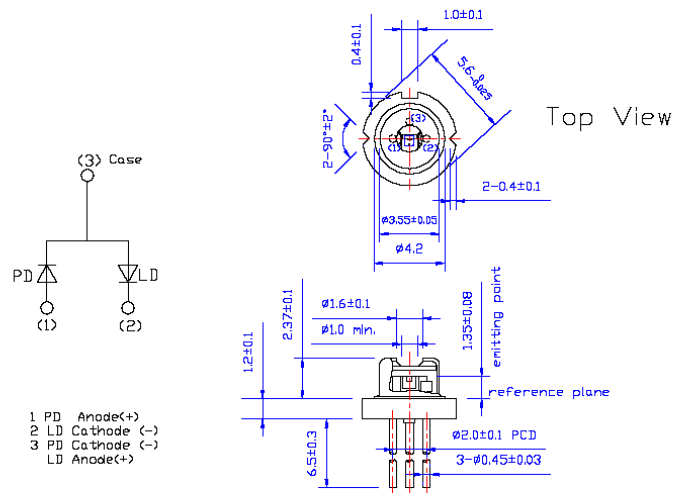


S9810MG

■ Specifications

- (1) Device: Laser Diode
 (2) Structure: TO-18 (ϕ 5.6mm)

■ External dimensions(Unit : mm)



■ Absolute Maximum Ratings(Tc=25°C)

Parameter	Symbol	Value	Unit
Optical Output	Po	10	mW
Reverse Voltage	Laser	Vr	V
	PIN PD	Vr(PIN)	30
Operating Temperature	Top	-10~+40	°C
Storage Temperature	Tstg	-15~+85	°C

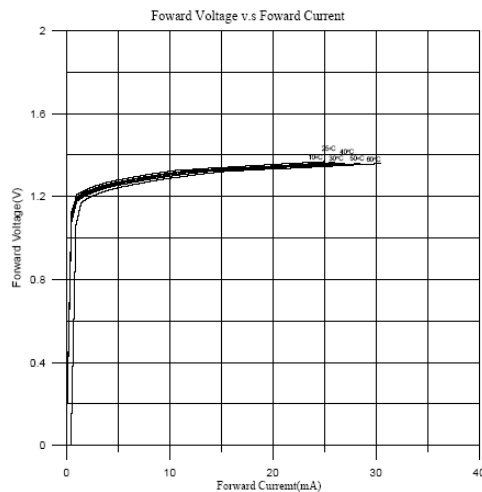
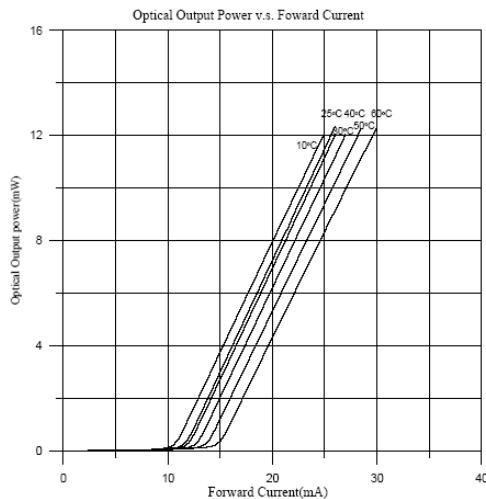


■ Electrical and Optical Characteristics(Tc=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Threshold Current	I _{th}	CW	-	12	20	mA	
Operating Current	I _{op}	P _o =10mW	-	25	40	mA	
Operating Voltage	V _{op}	P _o =10mW	-	1.5	2	Volt	
Slope Efficiency	η	7.5mW-2.5mW	0.5	0.8	-	mW/mA	
		I _{7.5mW} - I _{2.5mW}					
Monitor Current	I _m	P _o =10mW	0.02	0.03	0.5	mA	
Beam Divergence (FWHM)	Parallel	θ //	P _o =10mW	8	12	14	deg.
	Perpendicular	θ ⊥	P _o =10mW	25	32	40	deg.
Lasing Wavelength	λ	P _o =10mW	965	980	995	nm	

◎ θ // and θ ⊥ are defined as the angle within which the intensity is 50% of the peak value.

■ Typical characteristic curves





ROITHNER LASERTECHNIK GmbH

WIEDNER HAUPTSTRASSE 76 1040 VIENNA AUSTRIA
TEL. +43 1 586 52 43 -0, FAX. -44, OFFICE@ROITHNER-LASER.COM

